

Hyeonmin Jeon

SOFTWARE ENGINEER

Seoul, South Korea

☎ (+82) 10-4359-1959 | ✉ jeonhm1959@gmail.com

Currently Employed Samsung Electronics Foundry

Education

KAIST(Korea Advanced Institute of Science and Technology)

Daejeon, S.Korea

M.S. IN MATERIALS SCIENCE AND ENGINEERING

Mar. 2018 - Feb. 2020

- Thesis: Development of earth-abundant $\text{Cu}_2\text{ZnSnSe}_4$ solar cells on flexible titanium substrate
- Advisor: Seokwoo Jeon
- GPA : 3.61/4.3

KAIST(Korea Advanced Institute of Science and Technology)

Daejeon, S.Korea

B.S. IN CHEMICAL AND BIOMOLECULAR ENGINEERING

Mar. 2013 - Feb. 2018

- GPA : 3.56/4.3

Research Interest

Neuromorphic Devices, Heterogeneous Integration, Nanoelectronics

Research Experience

SF2 Logic device, M1 24P Task Force

S.Korea

SAMSUNG ELECTRONICS, FOUNDRY

Jun. 2025 - Sep. 2025

- Improved 2nm logic device yield through 24P (13 nm width, 11 nm space) BEOL(Back-End-of-line) process scheme optimization
- Developed SESL(Single Etch stopped layer) scheme in 2nm logic device

SF2 Logic device, BEOL Process Architecture

S.Korea

SAMSUNG ELECTRONICS, FOUNDRY

Jun. 2023 - May. 2025

- Developed SF2 (Samsung Foundry 2nm) Logic device BEOL interconnect part
- Enhanced SF2 logic device performance using CuMn and a thin Co liner
- Enhanced SF2 Logic Device performance with High density Low-k material in interconnection

SF3 Logic device, BEOL Process Architecture

S.Korea

SAMSUNG ELECTRONICS, SEMICONDUCTOR R&D CENTER/FOUNDRY

Mar. 2021 - MAY. 2023

- Replaced ALD barrier metal with reverse-selected barrier metal, reducing resistance and enhancing device performance
- Developed a self-aligned universal patterning process for the first, second, and third narrow-width BEOL metal layers

SF4 Logic device, BEOL Technology development

S.Korea

SAMSUNG ELECTRONICS, SEMICONDUCTOR R&D CENTER

Mar. 2020 - Feb. 2021

- Improved SF4 Logic device yield by Litho-Etch-Litho-Etch process combined with cut patterning
- Enhanced SF4 Logic device performance with ALD Barrier metal process

$\text{Cu}_2\text{ZnSnSe}_4$ Solar Cell

Daejeon, S.Korea

KAIST, KOREA INSTITUTE OF ENERGY RESEARCH (KIER)

Mar. 2018 - Feb. 2020

- Development of earth-abundant $\text{Cu}_2\text{ZnSnSe}_4$ solar cells on flexible titanium substrate
- effects of Film Growth Temperatures on Device Performances

Publications

Fabrication and Characterization of $\text{Cu}_2\text{ZnSnSe}_4$ Thin-Film Solar Cells Using a Single-Stage Co-Evaporation Method: Effects of Film Growth Temperatures on Device Performances

ENERGIES

Jan. 2020

- Muhammad Rehan, Hyeonmin Jeon, Yunae Cho, Ara Cho, Kihwan Kim, Jun-Sik Cho, Jae Ho Yun, Seungkyu Ahn, Jihye Gwak, Donghyeop Shin

Patents

Semiconductor device having via

SAMSUNG ELECTRONICS

- Patent No. 1020220173047

S.Korea

Dec. 2022

Conferences

GPVC (Global Photovoltaic Conference)

Gwangju, S.Korea

POSTER

Mar. 2019

- Effect of CdS Air-Annealing on the Performance of CZTSe Solar Cells

Honors & Awards

- 2026- **SAMSUNG**, Full funding for graduate school
- 2019 **KAIST**, KAIST support scholarship
- 2018 **KAIST**, KAIST support scholarship
- 2017 **KAIST**, KAIST support scholarship
- 2014-2016 **KAIST**, Merit-based KAIST support scholarship
- 2013 **KAIST**, KAIST support scholarship